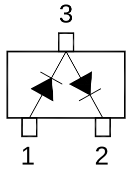
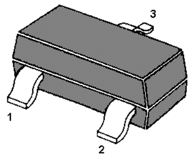
1SS226-AH

Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance
- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant





Marking Code: **A7**
1. Anode 1 2. Cathode 2
3. Anode 2 / Cathode 1
TO-236 Plastic Package

Applications

- Ultra high speed switching application

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1.2	V
Reverse Current at V_R = 80 V	I_R	0.5	µA
Total Capacitance at V_R = 0 , f = 1 MHz	C_T	3	pF
Reverse Recovery Time at I_F = 10 mA	t_{rr}	4	ns

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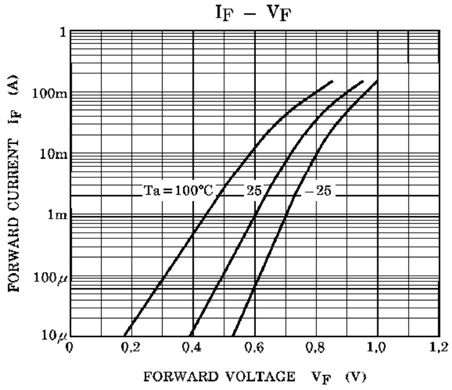
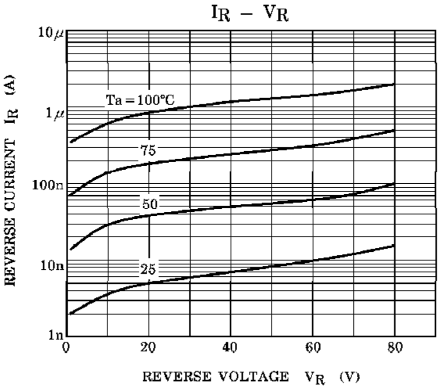
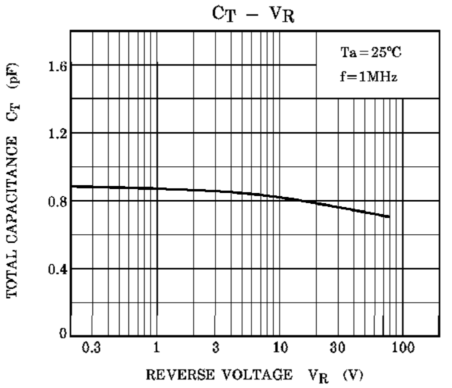
Dated: 23/10/2017 Rev: 01







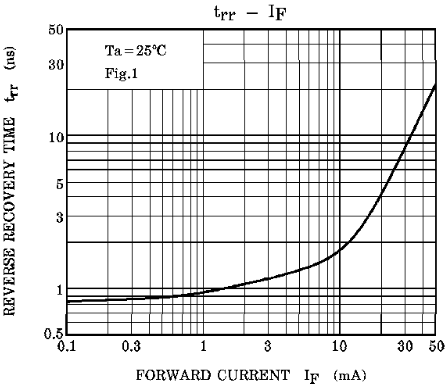


Fig.1 Reverse recovery time (t_{rr}) test circuit